504034156 10/04/2016

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
Yi-Liang Ye	08/19/2016
Kuang-Hsiu Chen	08/19/2016
Chun-Wei Yu	08/19/2016
Chueh-Yang Liu	08/19/2016
Yu-Ren Wang	08/19/2016

RECEIVING PARTY DATA

Name:	UNITED MICROELECTRONICS CORP.
Street Address:	No.3, Li-Hsin Road 2, Science-Based Industrial Park
City:	Hsin-Chu City
State/Country:	TAIWAN

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	15284552

CORRESPONDENCE DATA

Fax Number: (703)997-4517

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 3027291562

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Correspondent Name: WINSTON HSU **Address Line 1:** P.O.BOX 506

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ATTORNEY DOCKET NUMBER:	NAUP2841USA
NAME OF SUBMITTER:	SIBYL YU
SIGNATURE:	/SIBYL YU/
DATE SIGNED:	10/04/2016

Total Attachments: 10 source=2676141#page1.tif source=2676141#page2.tif source=2676141#page3.tif

PATENT 504034156 REEL: 039926 FRAME: 0675



PATENT REEL: 039926 FRAME: 0676

Title of Invention:

FINFET STRUCTURE AND FABRICATING METHOD OF GATE STRUCTURE

As the below named inventor, I here This declaration is directed to:	eby declare that:	
☑ The attached application, or	•	
☐ United States application nu	ımber	filed on, or
☐ PCT international application	n number	filed on
The above-identified application was	s made or authorized to be made	by me.
l believe that I am the original invent application.	tor or an original joint inventor of a	claimed invention in the
l hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr	Il false statement made in this dec risonment of not more than five (5)	elaration is punishable years, or both.
In consideration of the payment by	UNITED MICROELECTRON CORP.	IICS having a postal address of
No.3, Li-Hsin Road 2, Science	e-Based Industrial Park, Hsi	n-Chu City 300, Taiwan, R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good ar	o I of the sum of One Dollar (\$ 1.0 nd valuable consideration.	0), the receipt of which is hereby
I hereby sell, assign and transfer to a the entire right, title and interest in a invention as above-identified applica invention by the above application of substitutes, or extensions thereof, ar	nd to any and all improvements w ition and, in and to, all Letters Pat r any continuations, continuation-i	hich are disclosed in the ent to be obtained for said n-part, divisions, renewals.
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encumbran h this assignment;	ce has been or will be made or
I further covenant that ASSIGNEE wand documents relating to said inverknown and accessible to I and will terelated thereto and will promptly exe	ntion and said Letters Patent and lestify as to the same in any interfe	egal equivalents as may be rence, litigation proceeding
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WINTNESS WHEREOF, I have h	olication, said invention and said L ecessary or desirable to carry out t	etters Patent and said
Note: An application data sheet (PTC	D/SB/14 or equivalent), including r s form. Use this form for <u>each ad</u> c	naming the entire litional inventor.

Page 1 of 10

LEGAL NA	WE OF INVENTOR (ASSIGNOR)			
Inventor:	Yí-Liang Ye	Date:	2016/08/19	
Signature:	Ti-Liang Te			_

Page 2 of 10

F#NPO-P0002E-US1201 DSB0-105U022579

Title of Invention:

FINFET STRUCTURE AND FABRICATING METHOD OF GATE STRUCTURE

As the below named inventor, I here This declaration is directed to:	by declare that:			
☑ The attached application, or				
☐ United States application nu	mber	file	ed on	, or
☐ PCT international application	number		filed on	
The above-identified application was	made or authorized	to be made by n	ne.	
I believe that I am the original invente application.	or or <mark>an original join</mark> t	inventor of a cla	imed invention in the	
I hereby acknowledge that any willful under18 U.S.C. 1001 by fine or impri	l false statement ma sonment of not mon	de in this declara e than five (5) yea	ation is punishable ars, or both.	
In consideration of the payment by	UNITED MICRO	ELECTRONIC	S having a postal a	ddress of
No.3, Li-Hsin Road 2, Science	-Based Industria	I Park, Hsin-C	 Chu City 300, Taiwa	an, R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, and for other good an	l of the sum of One d valuable considera	Dollar (\$ 1.00), fation.	the receipt of which is	hereby
I hereby sell, assign and transfer to A the entire right, title and interest in an invention as above-identified application or substitutes, or extensions thereof, an	id to any and all imp iion and, in and to, a any continuations, o	rovements which II Letters Patent t continuation-in-pa	are disclosed in the to be obtained for said art, divisions, renewals	
I hereby covenant that no assignmen entered into which would conflict with	t, sale, agreement o this assignment;	r encumbrance h	nas been or will be mad	de or
I further covenant that ASSIGNEE wi and documents relating to said invent known and accessible to I and will test related thereto and will promptly exec	tion and said Letters stify as to the same i	Patent and lega	I equivalents as may b)e
representatives any and all papers, ir maintain, issue and enforce said appi equivalents thereof which may be ned IN WINTNESS WHEREOF, I have he	lication, said invention cessary or desirable	on and said Lette to carry out the p	rs Patent and said proposes thereof.	e of signing)
Note: An application data sheet (PTO inventive entity, must accompany this	//SB/14 or equivalen form. Use this form	t), including nam for <u>each additior</u>	ing the entire nal inventor.	

Page 3 of 10

NPO#NAU-P2841-USA:0 CUST#UMCD-2016-0331

F#NPO-P0002E-US1201 DSB0-105U022579

LEGAL NAI	ME OF INVENTOR(ASSIGNOR)	•	
Inventor:	Kuang-Hsiu Chen	Date:	AUG 1 9 2016
Signature:	Kung- Ham Chen		

Page 4 of 10

Title of Invention:

FINFET STRUCTURE AND FABRICATING METHOD OF GATE STRUCTURE

As the below named inventor, I here This declaration is directed to:	by declare that:			
☑ The attached application, or				
☐ United States application nu	mber	file	d on	, or
☐ PCT international application	number		filed on	***************************************
The above-identified application was	made or authorized to	be made by m	ne.	
I believe that I am the original invente application.	or or an original joint in	nventor of a clai	med invention i	n the
I hereby acknowledge that any willful under18 U.S.C. 1001 by fine or impri	I false statement made sonment of not more t	e in this declarat han five (5) yea	tion is punishab irs, or both.	le
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No.3, Li-Hsin Road 2, Science	-Based Industrial	Park, Hsin-C	 hu City 300,	Taiwan, R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an I hereby sell, assign and transfer to A the entire right, title and interest in an invention as above-identified application or	d valuable considerating some summer was some some some summer and the summer and to any and any continuations. co	on. ccessors and as vements which Letters Patent to ntinuation-in-pa	ssignees of the are disclosed in to be obtained for	ASSIGNEE of the or said
substitutes, or extensions thereof, an	d as to Letters Patent	any reissue or r	e-examination	thereof.
I hereby covenant that no assignmen entered into which would conflict with	t, sale, agreement or e this assignment;	encumbrance ha	as been or will t	oe made or
I further covenant that ASSIGNEE wi and documents relating to said invent known and accessible to I and will tes related thereto and will promptly exec	tion and said Letters F stify as to the same in	atent and legal anv interference	equivalents as	may he
representatives any and all papers, ir maintain, issue and enforce said appl equivalents thereof which may be ned IN WINTNESS WHEREOF, I have he	ication, said invention cessary or desirable to	and said Letter carry out the p	s Patent and sa	aid f. (Date of signing)
Note: An application data sheet (PTO inventive entity, must accompany this	/SB/14 or equivalent), form. Use this form fo	including namin	ng the entire al inventor.	

Page 5 of 10

LEGAL NAI	ME OF INVENTOR(AS	NOR)	
Inventor:	Chun-Wei Yu	Date:	AUG 1 9 2016
Signature:	Chan-Wei	M	

Page 6 of 10

Title of Invention:

FINFET STRUCTURE AND FABRICATING METHOD OF GATE STRUCTURE

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	_filed on	, or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made	by me.	***************************************
I believe that I am the original inventapplication.	or or an original joint inventor of a	claimed invention in the	
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(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	I of the sum of One Dollar (\$ 1.0 d valuable consideration.	0), the receipt of which is her	reby
I hereby sell, assign and transfer to A the entire right, title and interest in an invention as above-identified application or substitutes, or extensions thereof, an	id to any and all improvements with ion and, in and to, all Letters Pate any continuations, continuation-industrians to Letters Patent any reissued as to Letters Patent any reissued.	hich are disclosed in the ent to be obtained for said n-part, divisions, renewals, e or re-examination thereof.	
I hereby covenant that no assignmen entered into which would conflict with	t, sale, agreement or encumbran this assignment;	ce has been or will be made	or
I further covenant that ASSIGNEE wi and documents relating to said invent known and accessible to I and will tes related thereto and will promptly exec	tion and said Letters Patent and I stify as to the same in any interfe	egal equivalents as may be rence. litigation proceeding	s
representatives any and all papers, ir maintain, issue and enforce said appl equivalents thereof which may be ned IN WINTNESS WHEREOF, I have he	ication, said invention and said L cessary or desirable to carry out t	etters Patent and said he proposes thereof.	f signing)
Note: An application data sheet (PTO nventive entity, must accompany this	/SB/1 4 or equivalent), including n form. Use this form for <u>each add</u>	aming the entire itional inventor.	

Page 7 of 10

NPO#NAU-P2841-USA:0 CUST#UMCD-2016-0331

F#NPO-P0002E-US1201 DSB0-105U022579

LEGAL NAI	ME OF INVENTOR(ASSIGNOR)					
Inventor:	Chueh-Yang Liu		Date:	AUG	1 '	2016	منتشد ومدة ومسهوس و
Signature:	Chueh - Yang	Lin					

Page 8 of 10

Title of Invention:

FINFET STRUCTURE AND FABRICATING METHOD OF GATE STRUCTURE

As the below named inventor, I here This declaration is directed to:	by declare that:			
☑ The attached application, or				
☐ United States application nu	mber	filed on	, or	
☐ PCT international application	filed on			
The above-identified application was	made or authorized to be made	de by me.		
I believe that I am the original invente application.	or or an original joint inventor o	of a claimed invention in the		
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impri	I false statement made in this o isonment of not more than five	declaration is punishable (5) years, or both.		
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(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	o I of the sum of One Dollar (\$ d valuable consideration.	1.00), the receipt of which is her	reby	
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I hereby covenant that no assignmen entered into which would conflict with	nt, sale, agreement or encumbr n this assignment;	rance has been or will be made	or	
I further covenant that ASSIGNEE wi and documents relating to said inven known and accessible to I and will te related thereto and will promptly exec	tion and said Letters Patent ar stify as to the same in any inte	nd legal equivalents as may be reference. litigation proceeding	ts	
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne N WINTNESS WHEREOF, I have he	lication, said invention and said cessary or desirable to carry o	d Letters Patent and said ut the proposes thereof.	f signing)	
Note: An application data sheet (PTC nventive entity, must accompany this	0/SB/14 or equivalent), includin s form. Use this form for <u>each ε</u>	ng naming the entire additional inventor.		

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F#NPO-P0002E-US1201 DSB0-105U022579

PATENT REEL: 039926 FRAME: 0685

LEGAL NAME OF INVENTOR(ASSIGNOR)						
Inventor:	Yu-Ren Wang	Date:	AUG	1 9	2016	
Signature:		inf				
	-					

Page 10 of 10

NPO#NAU-P2841-USA:0 CUST#UMCD-2016-0331

RECORDED: 10/04/2016

F#NPO-P0002E-US1201 DSB0-105U022579

PATENT REEL: 039926 FRAME: 0686